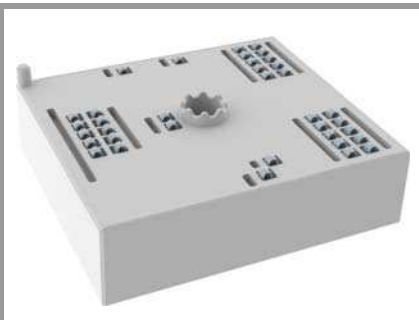


SKiiP 24GB17E4V1



MiniSKiiP® 2 Dual

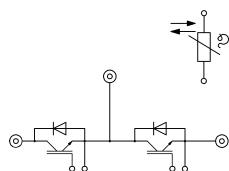
SKiiP 24GB17E4V1

Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- The creepage distance between T-Sensor and ground is 8mm



GB

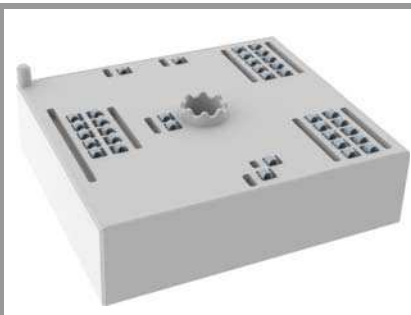
Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
Inverter - IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1700	V
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	177
		$T_s = 70^\circ\text{C}$	144
I_{Cnom}		150	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	450	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 1000\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1700\text{ V}$	$T_j = 150^\circ\text{C}$	10
T_j		-40 ... 175	$^\circ\text{C}$
Inverse - Diode			
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	149
		$T_s = 70^\circ\text{C}$	117
I_{Fnom}		150	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	300	A
I_{FSM}	10 ms, sin 180° , $T_j = 150^\circ\text{C}$	810	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$, 20 A per spring	200	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	2500	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 150\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.90	2.20	V
		$T_j = 150^\circ\text{C}$	2.30	2.60	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	7.3	8.7	m Ω
		$T_j = 150^\circ\text{C}$	11	12	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 6\text{ mA}$	5.2	5.8	6.4	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1700\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	13.60		nF
C_{oes}		$f = 1\text{ MHz}$	0.53		nF
C_{res}		$f = 1\text{ MHz}$	0.44		nF
Q_G	- 8 V... + 15 V		1200		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		4.3		Ω
$t_{d(on)}$	$V_{CC} = 900\text{ V}$ $I_C = 150\text{ A}$		225		ns
t_r	$R_{G on} = 2\text{ }\Omega$		40		ns
E_{on}	$R_{G off} = 2\text{ }\Omega$		26		mJ
$t_{d(off)}$	$di/dt_{on} = 4817\text{ A}/\mu\text{s}$		590		ns
t_f	$di/dt_{off} = 1088\text{ A}/\mu\text{s}$		148		ns
E_{off}	$du/dt = 5548\text{ V}/\mu\text{s}$ $V_{GE} = +15/-15\text{ V}$ $L_s = 25\text{ nH}$		46		mJ
					mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W/K}\cdot\text{m}$		0.28		K/W

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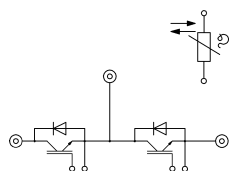
Features

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- Max. case temperature limited to $T_C=125^{\circ}\text{C}$
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- The creepage distance between T-Sensor and ground is 8mm

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
V _F = V _{EC}	I _F = 150 A	T _j = 25 °C		2	2.4	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.1	2.6	V
V _{F0}	chiplevel	T _j = 25 °C		1.3	1.6	V
		T _j = 150 °C		1.1	1.2	V
r _F	chiplevel	T _j = 25 °C		4.5	5.6	mΩ
		T _j = 150 °C		7.1	9	mΩ
I _{RRM}	I _F = 150 A			252		A
Q _{rr}	di/dt _{off} = 5270 A/μs			48.8		μC
E _{rr}	V _{GE} = -15 V			32.4		mJ
	V _{CC} = 900 V					
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/K*m			0.41		K/W
Module						
L _{CE}				20		nH
M _s	to heat sink		2		2.5	Nm
w				50		g
Temperature Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{25/85}	R(T)=R ₂₅ *exp[B _{25/85} *(1/T-1/298)], [T]=K			3420		K



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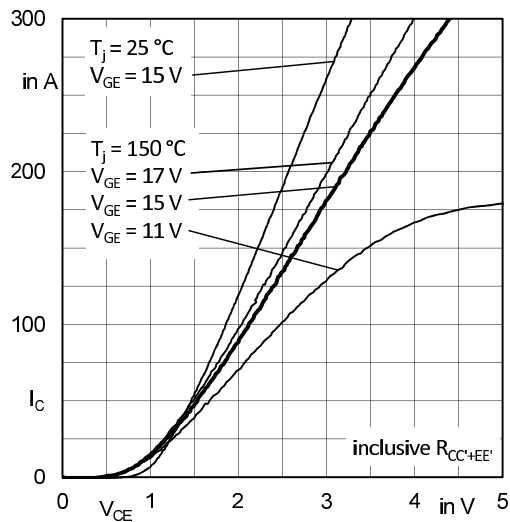


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

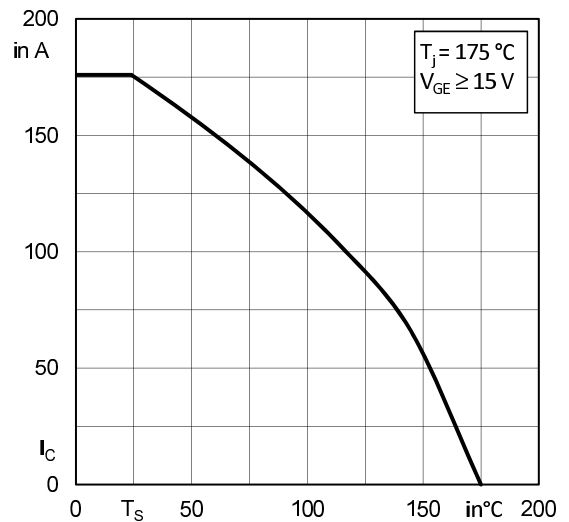


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

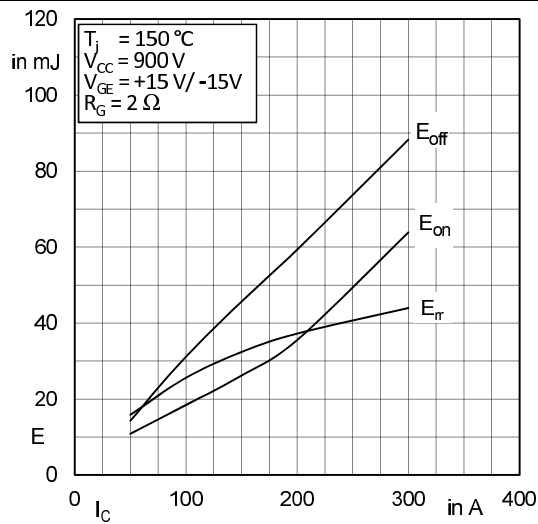


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

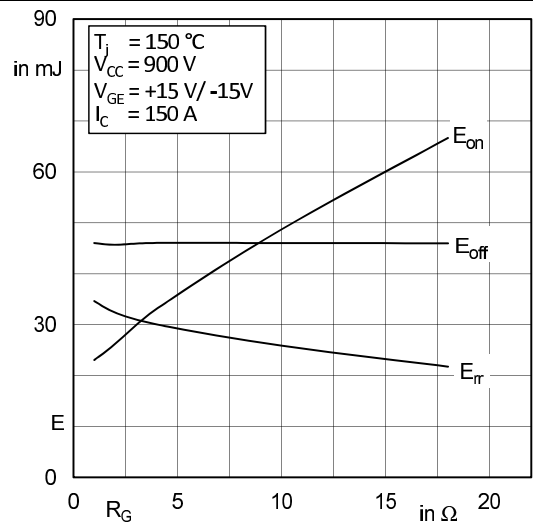


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

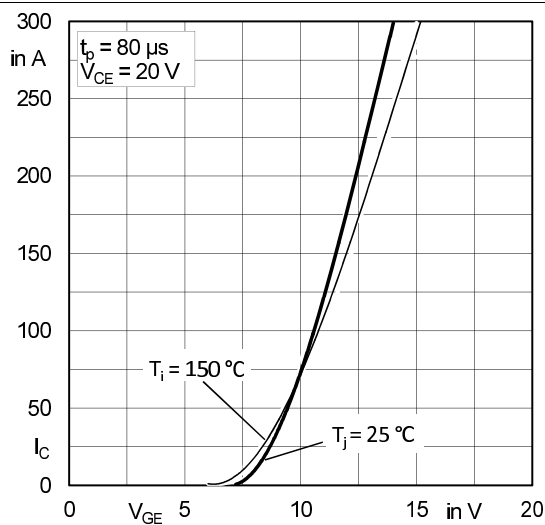


Fig. 5: Typ. transfer characteristic

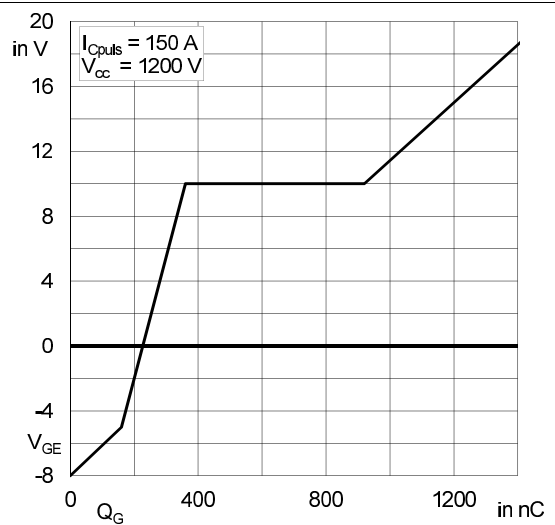


Fig. 6: Typ. gate charge characteristic

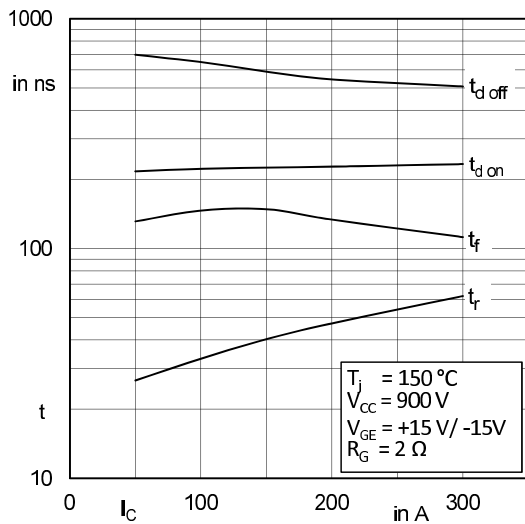


Fig. 7: Typ. switching times vs. I_C

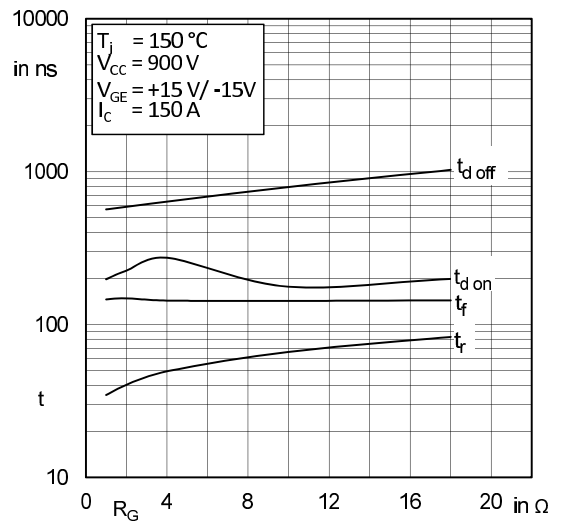


Fig. 8: Typ. switching times vs. gate resistor R_G

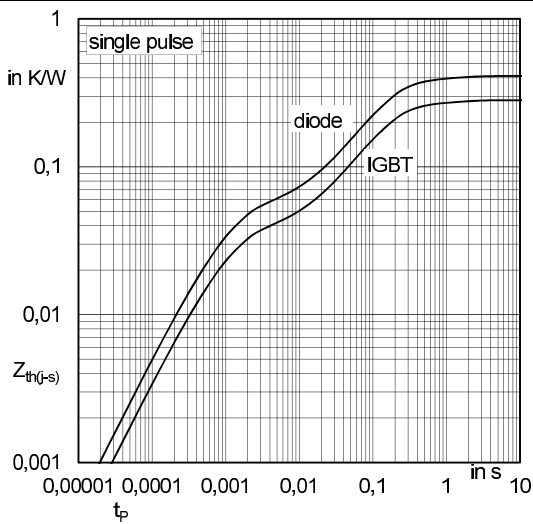


Fig. 9: Transient thermal impedance of IGBT and Diode

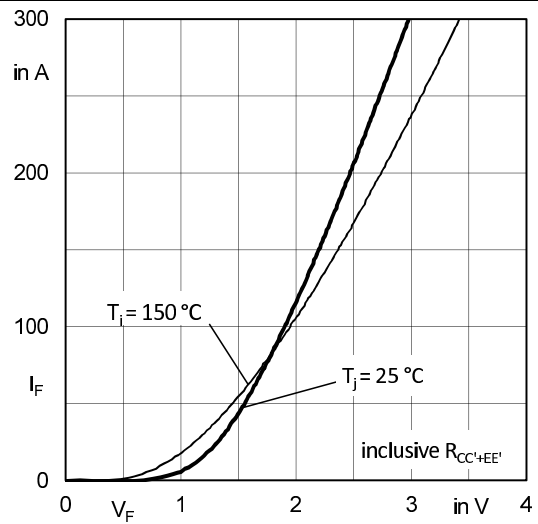


Fig. 10: CAL diode forward characteristic

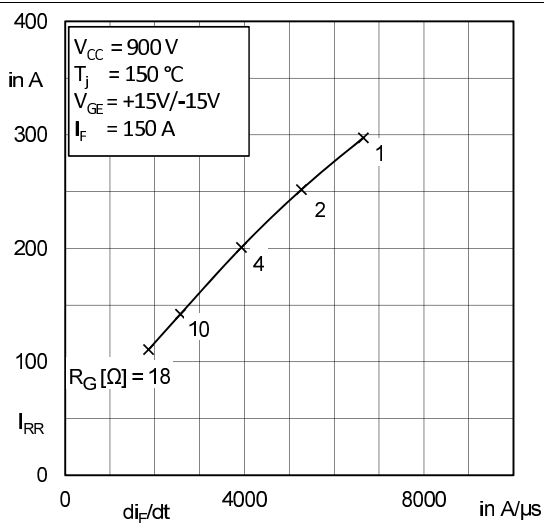


Fig. 11: Typ. CAL diode peak reverse recovery current

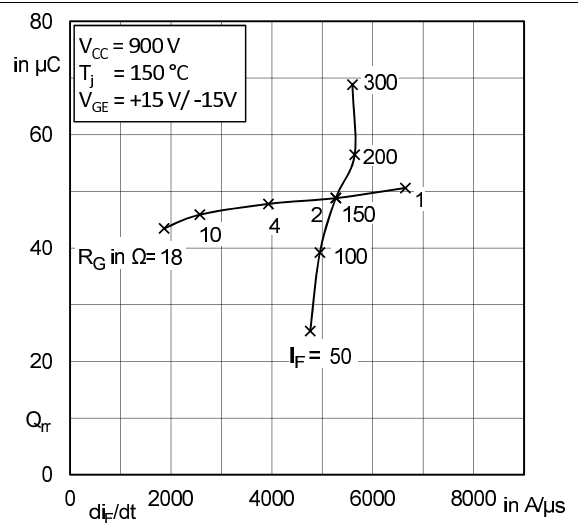
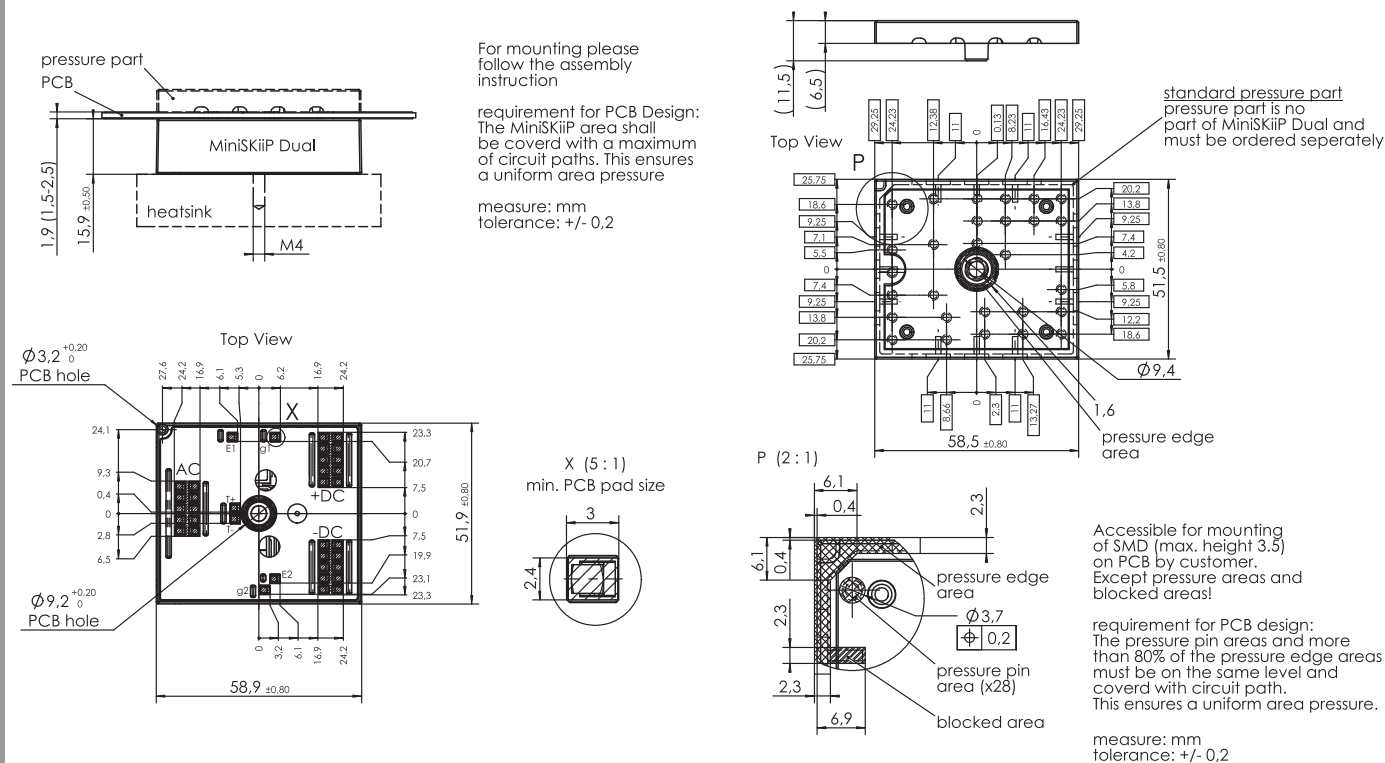
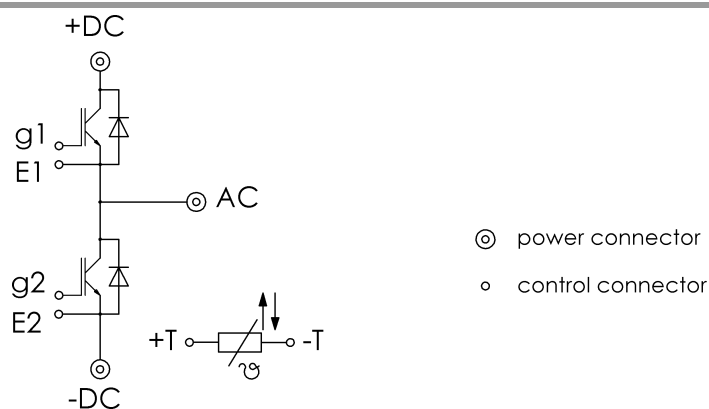


Fig. 12: Typ. CAL diode recovery charge



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.